Course : RF Microelectronics

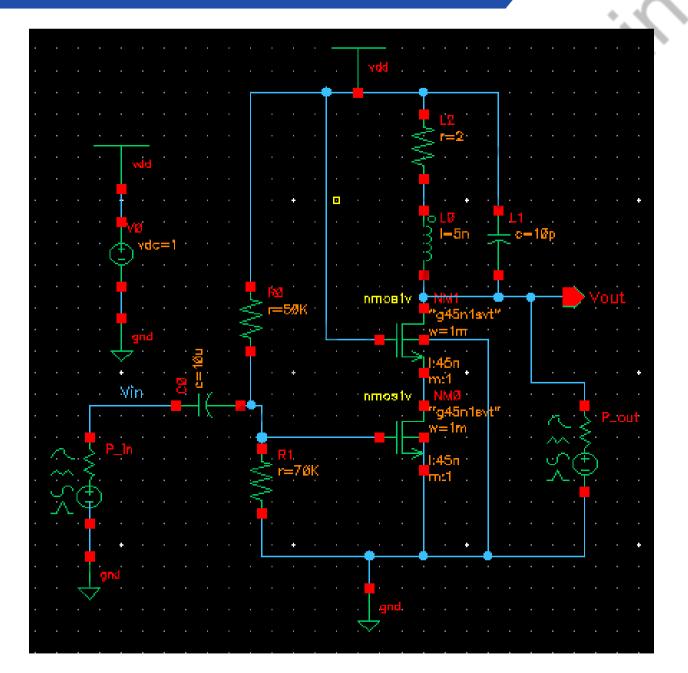
Lecture 3: Low Nosie Amplifiers

Prof. Sanjay Vidhyadharan



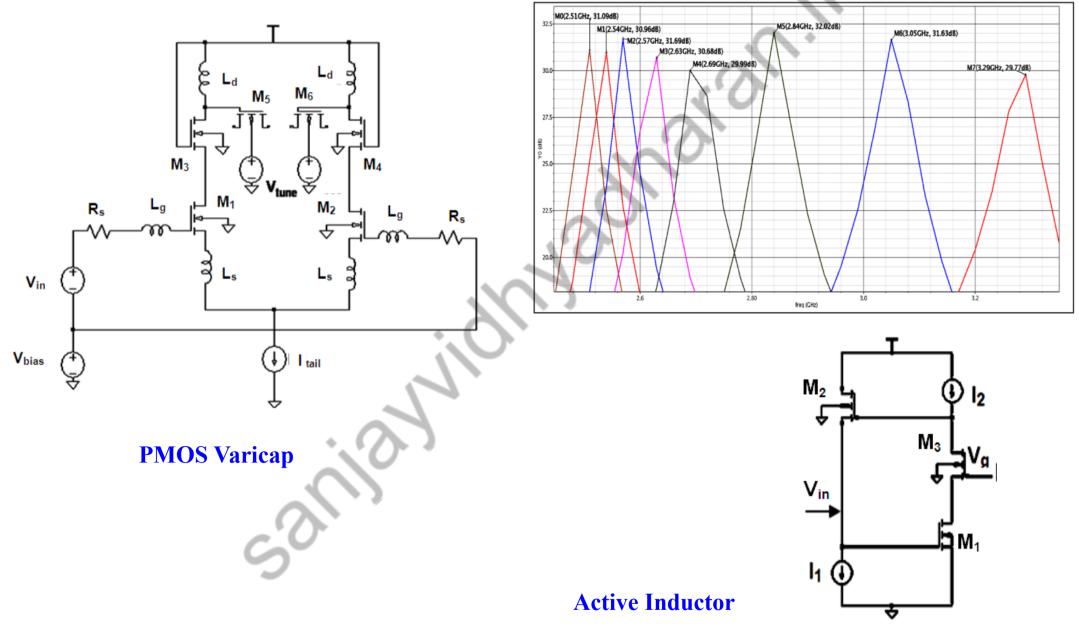
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Figure of Merits

- AC gain, centre freq and bandwidth
- Verification of gain with transient analysis 2.
- 3. **Nosie Figure**

https://sanjayvidhyadharan.in/courses/analog-ic-design/

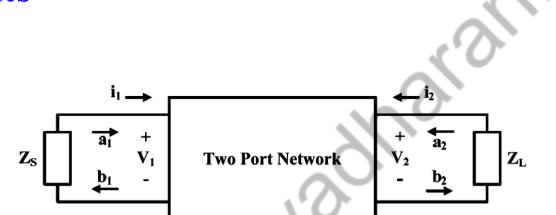
• The amount of noise added by the network is embodied in the Noise Factor F, which is defined by

Noise factor F = $\frac{\left(S_{N}\right)_{IN}}{\left(S_{N}\right)}$

F equals to 1 for noiseless network and in general F > 1. The noise figure in the noise factor quoted in dB Noise Figure F dB = $10 \log 10$ F $F \ge 0 dB$ i.e.

Figure of Merits

4. S-Parameters



 $\rightarrow S_{11} = b_1/a_1$ Network input reflection coefficient \int

- $S_{21} = b_2/a_1$ Forward gain
- $S_{22} = b_2/a_2$ Output reflection
- $S_{12} = b_1/a_2$ Reverse gain \leftarrow

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Design Steps for Input Matching

•Step 1: Chose a value below 10 nH for L_S (say 1 nH). Larger size spiral inductors in CMOS technology will be lossy and will occupy large silicon area.

•Step 2: Calculate ω_0 as per the formula given below for input impedance matching.

$$R_S = 50 = \omega_0 L_S$$

•Step 3: Calculate value of L_G as per the formula given below for desired value of Q (3dB band width BW_{3db}).

$$Q = \frac{f_0}{BW_{3dB}} = \frac{\left(L_G + L_S\right)\omega_0}{R_S}$$

•Step 4: Calculate C_{gs} as per the formula given below for obtaining the desired center frequency f_0 .

$$f_0 = \frac{1}{2\pi \sqrt{C_{gs}(L_G + L_S)}}$$

•Step 5: Calculate the width W 30f the input stage transistor knowing C_{ox} from technology and assigning appropriate L. (say 500 nm to avoid short channel effects)

•Step 6: Calculate g_m and I _{tail} using the formulae given below.

$$\mathbf{G}_{m} = \omega_{T} C_{gs} = \sqrt{2k_{n}' \left(\frac{W}{L}\right)_{n}} I_{DS}$$

